

SC-70 (3-LEADS)

Top View

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Ordering Information: Si1300BDL-T1-E3 (Lead (Pb)-free)

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**Vishay Siliconix** 

## N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}$ (Ω) $I_D$ (A) <sup>a</sup>		Q <sub>g</sub> (Typ.)	
20	0.85 at $V_{GS}$ = 4.5 V	0.4	0.335	
	1.08 at V <sub>GS</sub> = 2.5 V	0.35	0.335	

Marking Code

Si1300BDL-T1-GE3 (Lead (Pb)-free and Halogen-free)

Part # Code

Lot Traceability and Date Code

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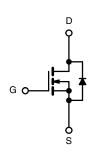
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



HALOGEN

FREE Available



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	<b>5</b> (1 <sub>A</sub> = 25 °C, unle	ess otherwise no	ited)	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	20	v
Gate-Source Voltage		V <sub>GS</sub>	± 8	v
	T <sub>C</sub> = 25 °C		0.4	
Continuous Drain Current (T 150 °C)	T <sub>C</sub> = 70 °C		0.32	
Continuous Drain Current ( $T_J = 150 \ ^{\circ}C$ )	T <sub>A</sub> = 25 °C	I <sub>D</sub>	0.37 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C		0.30 <sup>b, c</sup>	А
Pulsed Drain Current		I <sub>DM</sub>	0.5	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C		0.18	
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	0.14 <sup>b, c</sup>	
	T <sub>C</sub> = 25 °C		0.2	
Maximum Power Dissipation	T <sub>C</sub> = 70 °C		0.14	w
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.19	- vv
	T <sub>A</sub> = 70 °C		0.12 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	$t \le 5 s$	R <sub>thJA</sub>	540	670	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	450	570	0/11	

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 360  $^{\circ}\text{C/W}.$ 

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# Si1300BDL

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	• •		•	•	•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$	20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$			20		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA		- 2.8			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	0.4		1.0	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			100	nA	
	IDSS	$V_{DS}$ = 20 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			5	μΑ	
On-State Drain Current <sup>a</sup>		$V_{DS} \ge 5$ V, $V_{GS} = 4.5$ V	0.4			•	
	I <sub>D(on)</sub>	$V_{DS} \ge 5$ V, $V_{GS}$ = 2.5 V	0.12			A	
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 4.5 \text{ V}, I_D = 0.25$		0.65	0.85		
	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 0.15$		0.85	1.08	Ω	
Dynamic <sup>b</sup>						•	
Input Capacitance	C <sub>iss</sub>			35		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		13			
Reverse Transfer Capacitance	C <sub>rss</sub>			4			
Tabal Qada Ohamu	Qg	$V_{DS} = 10$ V, $V_{GS} = 4.5$ V, $I_{D} = 0.4$		560 840			
Total Gate Charge				335	503	pC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 2.5 V, $I_{D}$ = 0.35		98			
Gate-Drain Charge	Q <sub>gd</sub>			85			
Gate Resistance	Rg	f = 1 MHz	1.5	7	12	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			7	12		
Rise Time	t <sub>r</sub>	$V_{DD} = 10 \text{ V}, \text{ R}_{\text{I}} = 25 \Omega$		10	15	- ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 0.4$ Å, $V_{GEN} = 4.5$ V, $R_g = 1 \Omega$		8	13		
Fall Time	t <sub>f</sub>			7	12		
Drain-Source Body Diode Characteristic	s			•			
Continuous Source-Drain Diode Current	ا <sub>S</sub>	T <sub>C</sub> = 25 °C			0.18		
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				0.4	A	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.05 A		0.7	1.2	V	

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

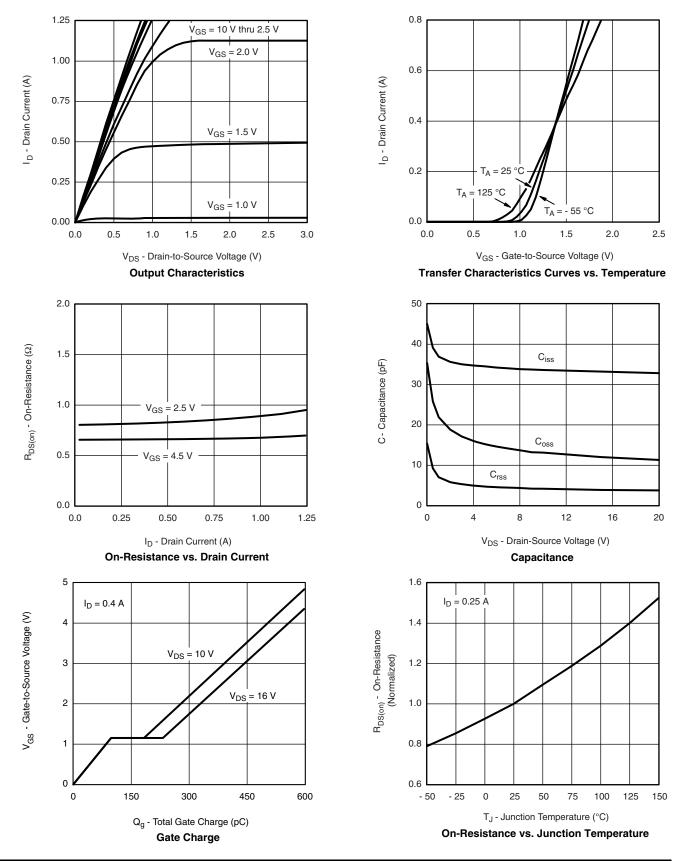
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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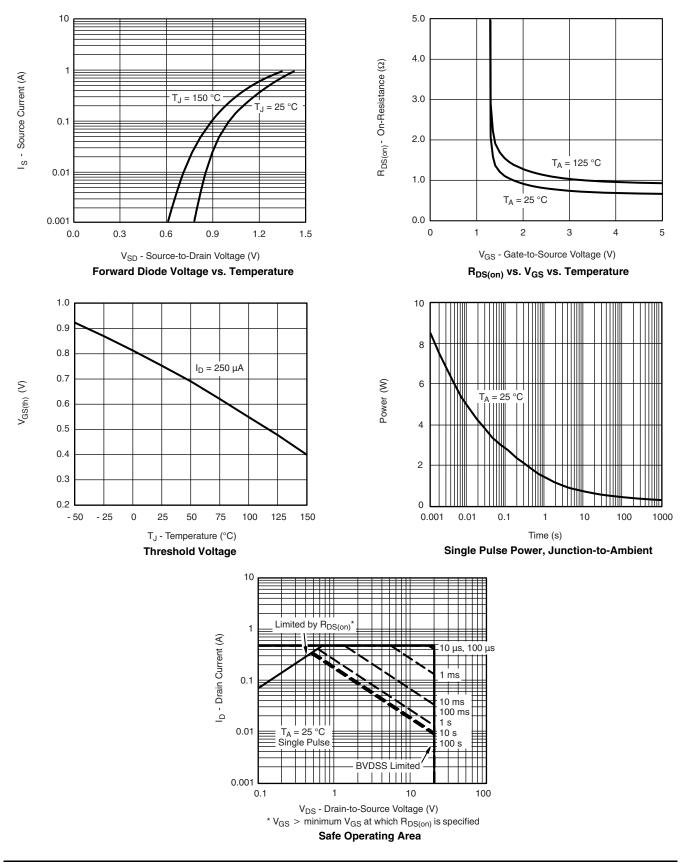
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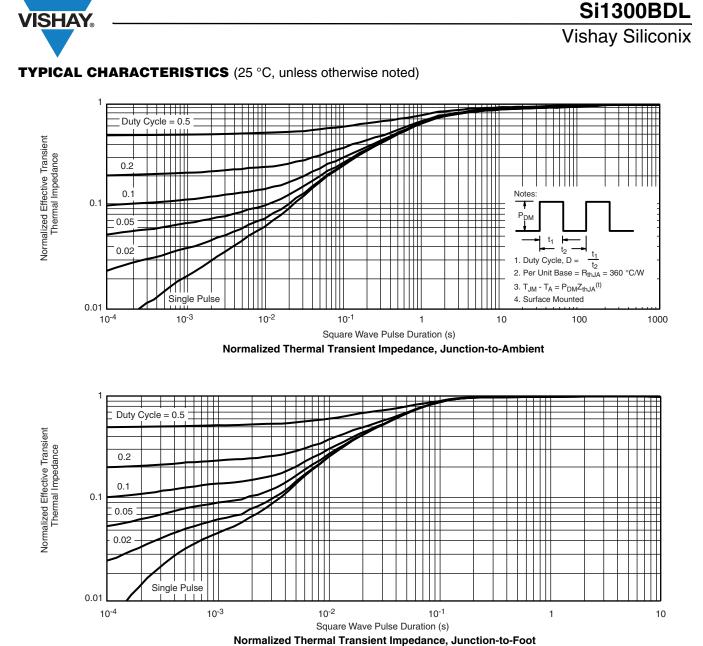


#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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